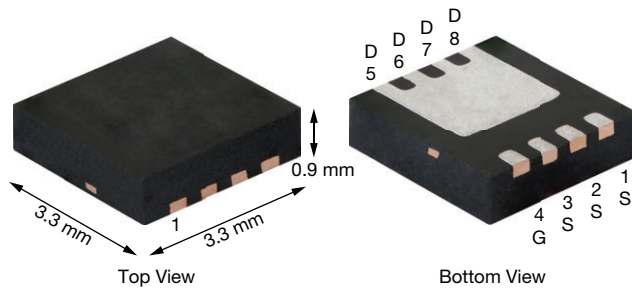




**THE DATASHEET OF
SISH108DN-T1-GE3**



N-Channel 20 V (D-S) Fast Switching MOSFET

PowerPAK® 1212-8SH


PRODUCT SUMMARY	
V_{DS} (V)	20
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.0049
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5$ V	0.0061
Q_g typ. (nC)	20
I_D (A)	22
Configuration	Single

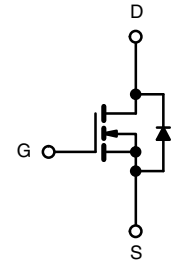
FEATURES

- TrenchFET® Gen II power MOSFET for ultra low on-resistance
- 100 % R_g tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
 COMPLIANT
 HALOGEN
FREE

APPLICATIONS

- Synchronous rectification
- Point-of-load converters
- Protection devices
- Hot swap



N-Channel MOSFET

ORDERING INFORMATION

Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH108DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	10 s	STEADY STATE	UNIT
Drain-source voltage	V_{DS}	20	20	V
Gate-source voltage	V_{GS}	± 16	± 16	
Continuous drain current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	22	A
		$T_A = 70$ °C	17.6	
Pulsed drain current	I_{DM}	60	60	A
Continuous source current (diode conduction) ^a	I_S	3.2	1.3	
Single avalanche current	I_{AS}	L = 0.1 mH	22	mJ
Single avalanche energy			E_{AS}	
Maximum power dissipation ^a	P_D	$T_A = 25$ °C	3.8	W
		$T_A = 70$ °C	2.0	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150		°C
Soldering recommendations (peak temperature) ^{b, c}		260		

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	R_{thJA}	$t \leq 10$ s	24	°C/W
		Steady state	65	
Maximum junction-to-case (drain)	R_{thJC}	1.9	2.4	

Notes

- Surface mounted on 1" x 1" FR4 board
- See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	-	2	V
Gate body leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	-	-	5	
On-state drain current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	40	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 22\text{ A}$	-	0.0041	0.0049	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 19.7\text{ A}$	-	0.0050	0.0061	
Forward transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 22\text{ A}$	-	88	-	S
Diode forward voltage ^a	V_{SD}	$I_S = 3.2\text{ A}, V_{GS} = 0\text{ V}$	-	0.75	1.2	V
Dynamic ^b						
Total gate charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 22\text{ A}$	-	20	30	nC
Gate-source charge	Q_{gs}		-	6.3	-	
Gate-drain charge	Q_{gd}		-	4.9	-	
Gate resistance	R_g	$f = 1\text{ MHz}$	0.7	1.4	2.1	Ω
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 20\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	-	10	15	ns
Rise time	t_r		-	10	15	
Turn-off delay time	$t_{d(off)}$		-	60	130	
Fall time	t_f		-	10	15	
Source-drain reverse recovery time	t_{rr}	$I_F = 3.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	30	60	nC
Reverse recovery charge	Q_{rr}		-	20	36	

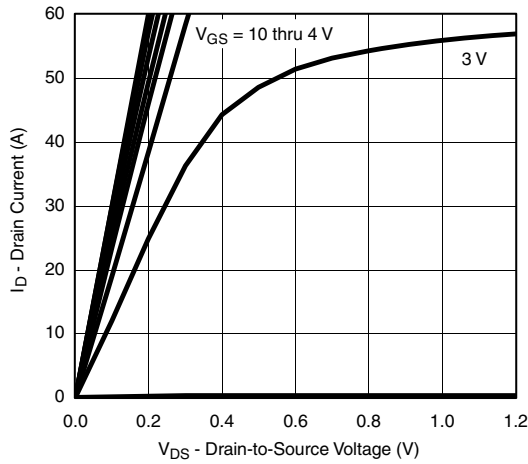
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing

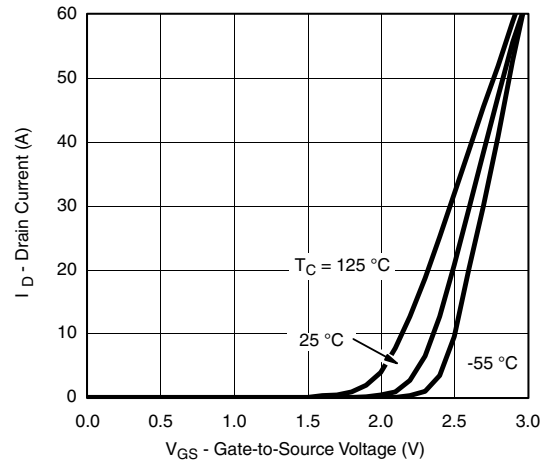
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



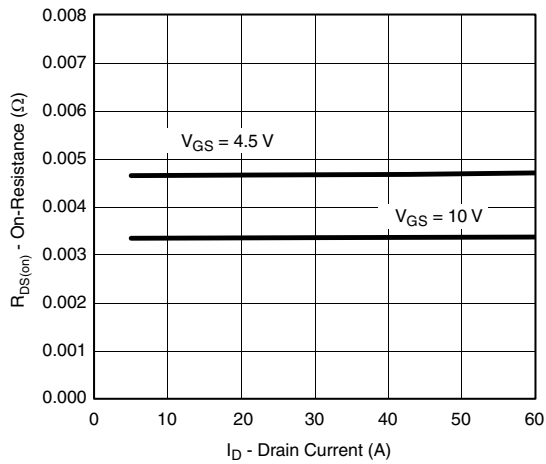
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



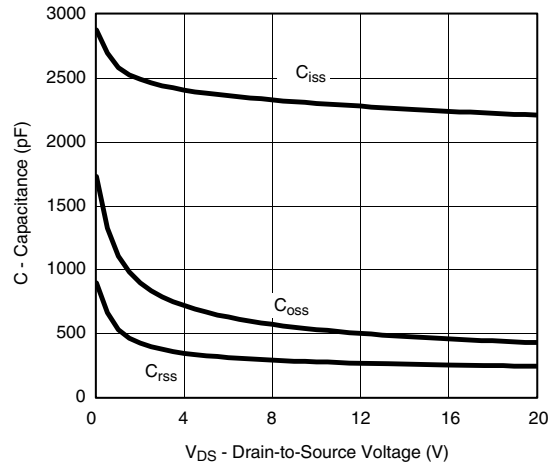
Output Characteristics



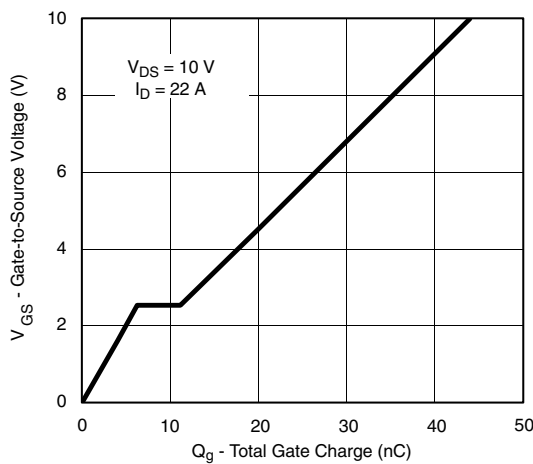
Transfer Characteristics



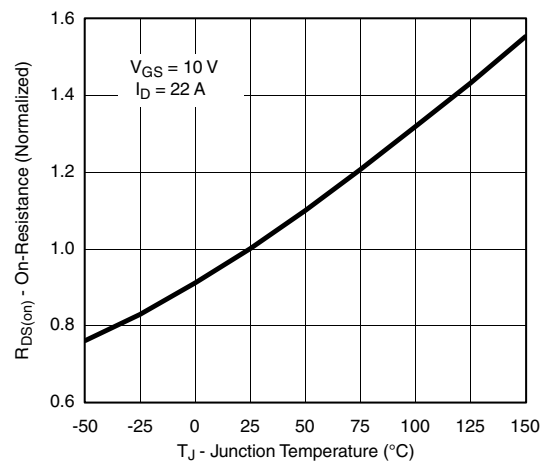
On-Resistance vs. Drain Current



Capacitance



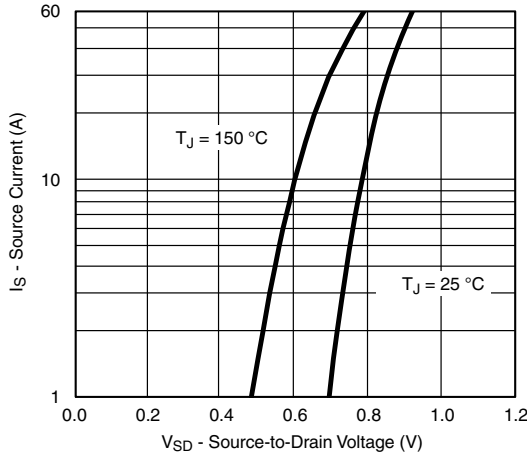
Gate Charge



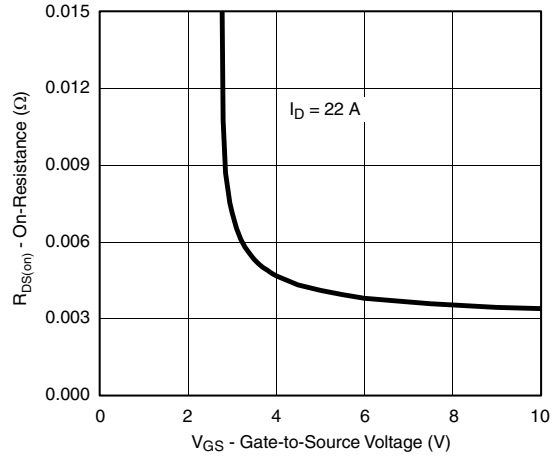
On-Resistance vs. Junction Temperature



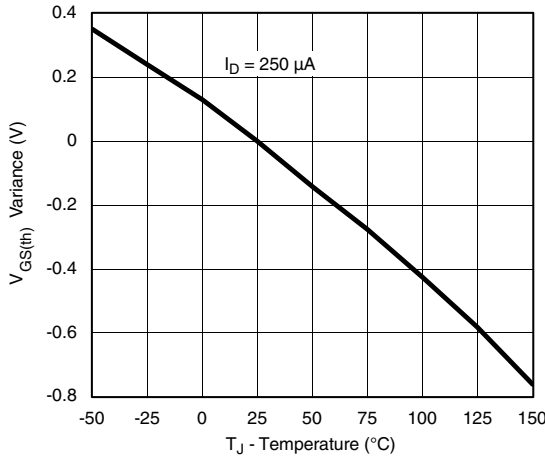
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



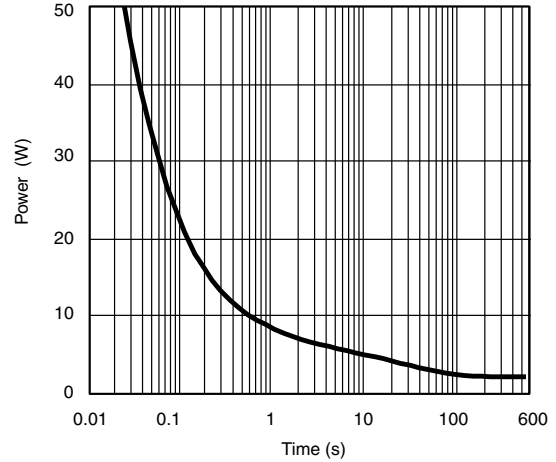
Source-Drain Diode Forward Voltage



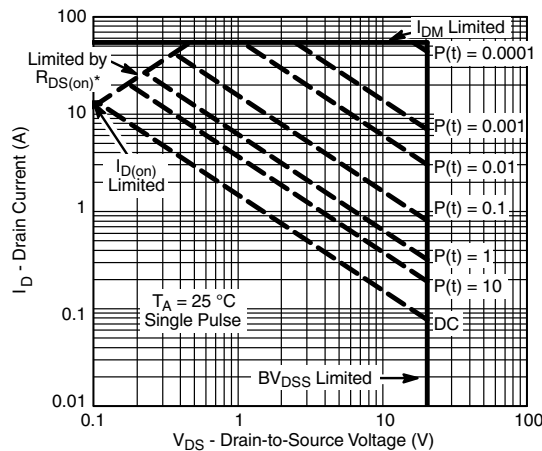
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

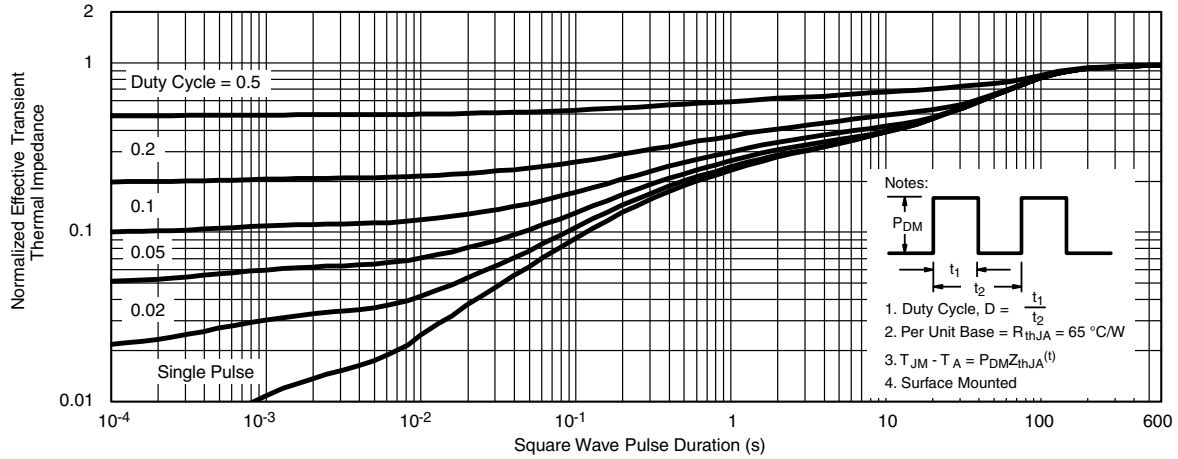


* VGS > minimum VGS at which RDS(on) is specified

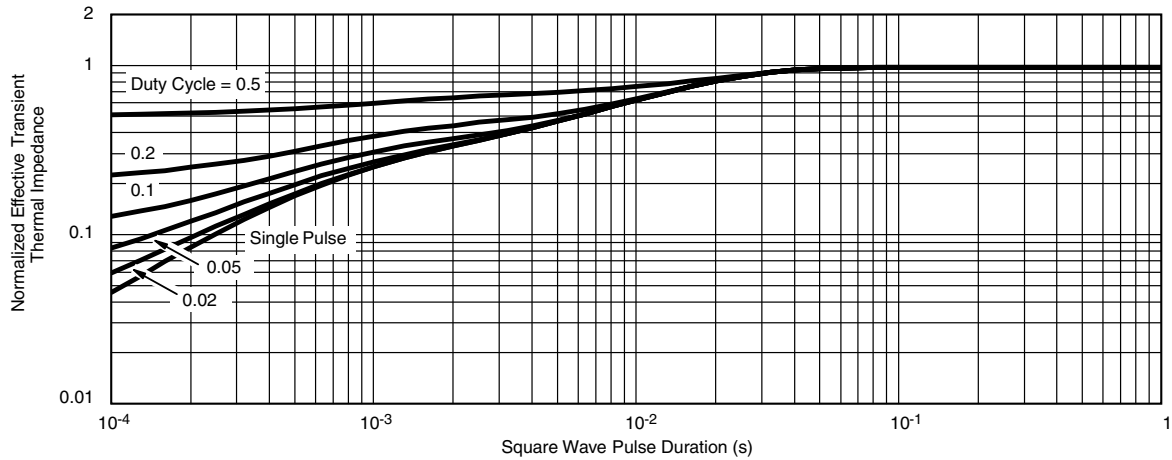
Safe Operating Area



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



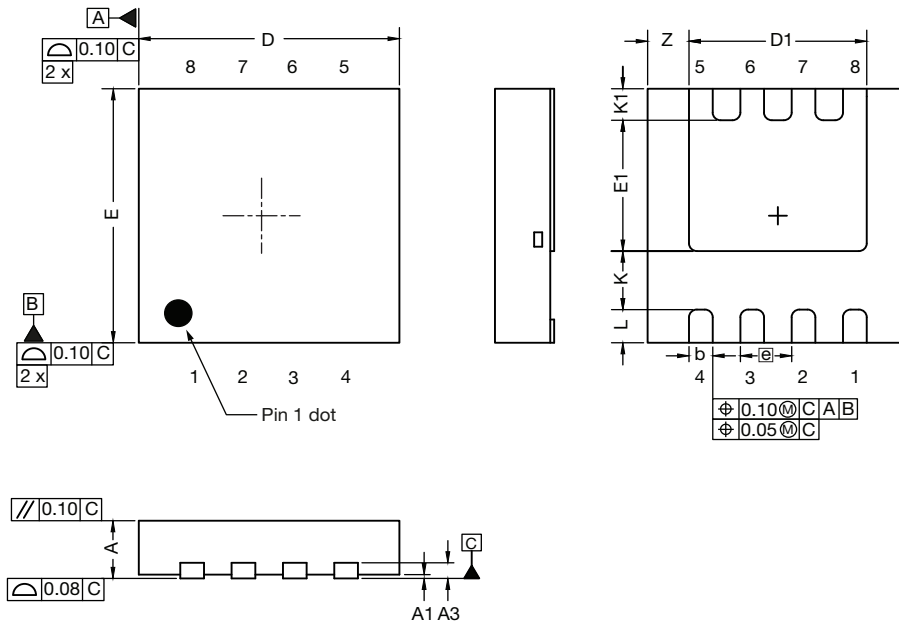
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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Case Outline for PowerPAK® 1212-SWLH and PowerPAK® 1212-8SH



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.82	0.90	0.98	0.032	0.035	0.038
A1	0.00	-	0.05	0.000	-	0.002
A3	0.20 ref.			0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.15	2.25	2.35	0.085	0.089	0.093
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	1.60	1.70	1.80	0.063	0.067	0.071
e	0.65 bsc.			0.026 bsc.		
K	0.76 ref.			0.030 ref.		
K1	0.41 ref.			0.016 ref.		
L	0.33	0.43	0.53	0.013	0.017	0.021
Z	0.525 ref.			0.021 ref.		

ECN: S20-0930-Rev. C, 07-Dec-2020
DWG: 6062

RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads
Dimensions in Inches/(mm)

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